

# **ABSTRACT OF THE DISCLOSURE**

An electrostatic discharge (ESD) protection device with enhanced ESD robustness. The ESD protection device comprises a pad, a finger-type MOS, a well stripe and a doped segment. The pad is on a semiconductor substrate of a first-conductive type. The finger-type MOS is on the semiconductor substrate and comprises drain regions, source regions and channel regions. Each drain region is of a second-conductive type and is coupled to the pad. Each source region is of the second-conductive type and coupled to a power rail. Channel regions are formed on the semiconductor, substantially parallel to each other. Each channel region is located between one source region and one drain region. The well stripe is of the second-conductive type and formed on the semiconductor, in an angle to the channel regions. The doped segment is of the first-conductive type and in the well stripe. Furthermore, the doped segment is coupled to the pad.